

AMENDMENT AND RESPONSE

Serial Number: 08/636,069

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Title: METHOD TO REDUCE FIXED CHARGE IN CVD OZONE DEPOSITED FILMS

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Dkt: 303.573US1

51. (Once amended) A method of depositing a silicon dioxide layer on a substrate surface, comprising:
contacting the substrate surface with a reaction volume of gas comprising a SiO₂ precursor and ozone; [and]
heating the substrate surface to a temperature of about 480°C to 700°C; and
illuminating the reaction volume of gas from a light source comprising mercury arc vapor lamps without directly exposing the substrate surface to the light source.
52. (Once amended) A method of depositing a doped silicon dioxide layer on a substrate surface, comprising:
contacting the substrate surface with a reaction volume of gas comprising a SiO₂ precursor, ozone and at least one dopant source; [and]
heating the substrate surface to a temperature of about 480°C to 700°C; and
illuminating the reaction volume of gas from a light source comprising mercury arc vapor lamps without directly exposing the substrate surface to the light source.

REMARKS

Applicant has carefully reviewed and considered the Office Action mailed on June 15, 1999, and the references cited therewith.

Claims 31, 42, 51 and 52 are amended. Claims 1, 2, 4-10 and 31-54 are now pending in the application.

Rejections Under 35 U.S.C. § 103**Claims 31, 33, 34, 36, 39, 40 and 42**

Claims 31, 33, 34, 36, 39, 40 and 42 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Hisamune (JP 2-050966).

Claims 31 and 42 have been amended to recite heating the substrate surface to a temperature of about 480°C to 700°C. Applicant respectfully submits that support for the